Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	(non adj volatile) and falsh	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:30
L3	483783	(electrically adj3 memory) or (erasable adj3 memory) or ($1eprom) or (flash or non-volatile or (non adj volatile) adj3 (memory or cell)) or ((non adj volatile) or nonvolatile or non-volatile) adj3 (memory or cell) or nvm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:04
L4	1206	365/185.21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
L5	24	4 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
L6	467	4 and ((non adj volatile) and flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L7	158	6 and ((memory adj cell adj matrix) or (column adj decoder))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
L8	7	7 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
L9	2314	365/185.18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L10	57	9 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07

L11	26	10 and ((non adj volatile) and flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L12	777	365/185.19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L13	11	12 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L14	1156	365/185.09	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L15	455	14 and ((non adj volatile) and flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
L16	4	15 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07
S1	480876	(electrically adj3 memory) or (erasable adj3 memory) or ($1eprom) or (flash or non-volatile or (non adj volatile) adj3 (memory or cell)) or ((non adj volatile) or nonvolatile or non-volatile) adj3 (memory or cell) or nvm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:45
S2	10582	voltage adj regulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
S3	1243	S1 and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:44
S4	14	S3 and (memory adj cell adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:57

S5	69	S3 and (column adj decoder)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:56
S6	78	S3 and ((memory adj cell adj matrix) or (column adj decoder))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
S7	36	(program$3 adj load adj circuit) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:24
S8	3	(non adj volatile) and falsh	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:30
S9	46361	(non adj volatile) and flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:05
S10	12273	S9 and eras$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:24
S11	11157	S10 and read$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:25
S12	8649	S11 and writ$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:25
S13	178	S12 and (program$3 adj load)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:25
S14	110	S13 and ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:31

S15	69	S14 and active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:27
S16	3	"6603681"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:30

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10/789351
Inventor: MARTINES , IGNAZIO, et al
Status: 30 - DOCKETED NEW CASE - READY FOR EXAMINATION
Title: VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY

Examiner: NGUYEN, NAM

GAU: 2824
Classification: 365/185.210

All tab report (16 items, not sorted)

Img	Status	Doc Code	Document Type	Date	Pages	Annotations
	7	PEFR	Applicant Response to Pre-Exam Formalities Notice	07/19/2004	7	
	7	OATH	Oath or Declaration filed	07/19/2004	3	
	7	FRPR	Foreign Priority Papers Filed	07/19/2004	1	
	7	IDS	Information Disclosure Statement (IDS) Filed	07/19/2004	3	considered 12/1/05
	7	NPL	NPL Documents	07/19/2004	6	
	7	FRPR	Foreign Priority Papers Filed	07/19/2004	20	
	7	PEFN	Pre-Exam Formalities Notice	05/19/2004	2	
	7	TRNA	Transmittal letter	02/26/2004	2	
	7	SPEC	Specification	02/26/2004	11	
	7	CLM	Claims	02/26/2004	5	
	7	ABST	Abstract	02/26/2004	1	
	7	DRW	Drawings	02/26/2004	5	
	7	OATH	Oath or Declaration filed	02/26/2004	1	
	7	WFEE	Fee Worksheet (PTO-875)	02/26/2004	1	

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Img	Status	Doc Code	Document Type	Date	Pages	Annotations
⊕	7	WFEE	Fee Worksheet (PTO-875)	02/26/2004	1	
⊕	7	ADS	Application Data Sheet	02/26/2004	2	